



IRLR3110ZPBF Information



For Reference Only

Part Number IRLR3110ZPBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 42A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRLR3110ZPBF Specifications

Manufacturer Part Number IRLR3110ZPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 100µA Gate Charge (Qg) (Max) @ Vgs 48nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 3980pF @ 25V Vgs (Max) 450 FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
CategoryDiscrete Semiconductor ProductsFansistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C42A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 100μAGate Charge (Qg) (Max) @ Vgs48nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 38A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	IRLR3110ZPBF
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C42A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 100μAGate Charge (Qg) (Max) @ Vgs48nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 38A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET Type Rochnology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 42A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 32.5V @ 100µA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature Supplier Device Package D-Pak Package / Case N-Channel NOSFET (Metal Oxide) 100V 42A (Tc) 44B (C e 4.5V 41B (C e 4	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C42A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 100μAGate Charge (Qg) (Max) @ Vgs48nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 38A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	HEXFET?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C42A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 100μAGate Charge (Qg) (Max) @ Vgs48nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 38A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature Supplier Device Package Package / Case 42A (Tc) 45°C 100μA 45V, 1	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 100μAGate Charge (Qg) (Max) @ Vgs48nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds3980pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)140W (Tc)Rds On (Max) @ Id, Vgs14 mOhm @ 38A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	42A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #16V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature Journal Type Surface Mount Supplier Device Package Package / Case 48nC @ 4.5V 3980pF @ 25V #16V #16V #16V FET Feature	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 3980pF @ 25V Vgs (Max) #16V FET Feature	Vgs(th) (Max) @ Id	2.5V @ 100μA
Vgs (Max) $\pm 16V$ FET Feature-Power Dissipation (Max) $140W$ (Tc)Rds On (Max) @ Id, Vgs 14 mOhm @ $38A$, $10V$ Operating Temperature $-55^{\circ}C \sim 175^{\circ}C$ (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO- 252 -3, DPak (2 Leads + Tab), SC- 63	Gate Charge (Qg) (Max) @ Vgs	48nC @ 4.5V
FET Feature - Power Dissipation (Max) 140W (Tc) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	3980pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 mOhm @ 38A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±16V
Rds On (Max) @ Id, Vgs14 mOhm @ 38A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	140W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	14 mOhm @ 38A, 10V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IRLR3110ZPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRLR3110ZPBF Payment Methods



















IRLR3110ZPBF Shipping Methods













If you have any question about IRLR3110ZPBF, please do not hesitate to contact us!

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